

L Number	Hits	Search Text	DB	Time stamp
1	637	374/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:47
2	180	374/55.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:47
3	78	374/56.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:29
4	1034	374/121.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
5	333	374/31.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
6	185	374/32.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
7	93	374/33.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
8	559	374/142.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
9	81	374/6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
10	118	374/7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:42
11	148	374/46.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02
12	332	356/601.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:02

13	132	356/608.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:03
14	45	324/451.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:03
15	207	324/452.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:03
16	1856	(piezoelectric) and temperature and radiation and deform\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:44
17	1057	(piezoelectric) and temperature and radiation and deform\$6 and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:45
18	237	(piezoelectric) and (temperature NEAR (detect\$3 or sens\$3)) and radiation and deform\$6 and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:45
19	124	374/45.ccls. and radiation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:47
20	20	374/55.ccls. and radiation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 11:47
21	9	374/56.ccls. and radiation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:20
22	1	374/56.ccls. and (silicon adj wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:25
24	3	374/55.ccls. and (silicon adj wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:21
23	13	374/45.ccls. and (silicon adj wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:21

25	1	374/56.ccls. and (electric\$3 adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:27
26	12	374/45.ccls. and (electric\$3 adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:27
27	1	374/55.ccls. and (electric\$3 adj field)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:27
28	37	374/56.ccls. and (wafer or ceramic or semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:34
29	28	374/55.ccls. and (wafer or ceramic or semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:34
30	344	374/\$.ccls. and piezoelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:42
31	116	374/\$.ccls. and piezoelectric and radiation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:42
32	106	374/\$.ccls. and piezoelectric and radiation and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:43
33	61	374/\$.ccls. and piezoelectric and radiation and temperature and length	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:44
34	0	374/\$.ccls. and piezoelectric and radiation and temperature and exoansion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:44
35	29	374/\$.ccls. and piezoelectric and radiation and temperature and expansion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:44